

### Description

The SI2312A is the high cell density trench N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

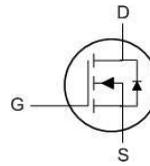
The SI2312A meet the RoHS and Green Product requirement with full function reliability approved.

$V_{DS}$  20 V  
 $I_D$  7 A  
 $R_{DS(ON)}$  12m $\Omega$

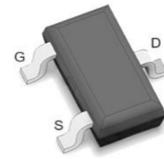
ANV

### Features

Green Device Available  
Super Low Gate Charge  
Excellent Cdv/dt effect decline  
Advanced high cell density Trench technology



Schematic Diagram



SOT-23-3L top view

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 4.5V <sup>1</sup>	7.0	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 4.5V <sup>1</sup>	5.0	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	32	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation <sup>3</sup>	2	W
$P_D@T_A=70^\circ\text{C}$	Total Power Dissipation <sup>3</sup>	0.66	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	120	$^\circ\text{C}/\text{W}$

## Electrical Characteristics ( $T_J=25^\circ\text{C}$ unless otherwise noted)

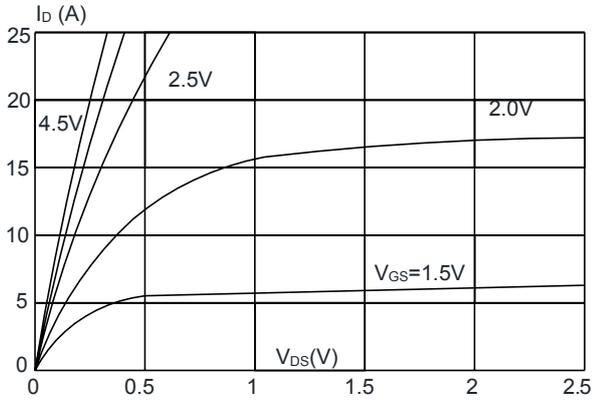
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.75	1.2	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=4.5V, I_D=6A$	-	12	15	m $\Omega$
		$V_{GS}=2.5V, I_D=5A$	-	16	22.5	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f=1.0MHz$	-	700	-	pF
$C_{oss}$	Output Capacitance		-	132	-	pF
$C_{rSS}$	Reverse Transfer Capacitance		-	114	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=10V, I_D=4A,$ $V_{GS}=4.5V$	-	15	-	nC
$Q_{gs}$	Gate-Source Charge		-	2	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	5.2	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V,$ $I_D=4A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	9	-	ns
$t_r$	Turn-on Rise Time		-	25	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	37	-	ns
$t_f$	Turn-off Fall Time		-	14	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	8	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=8A$	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

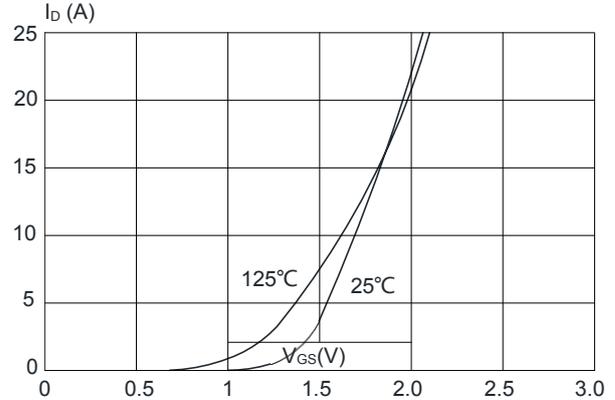
2. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

**RATING AND CHARACTERISTIC CURVES**

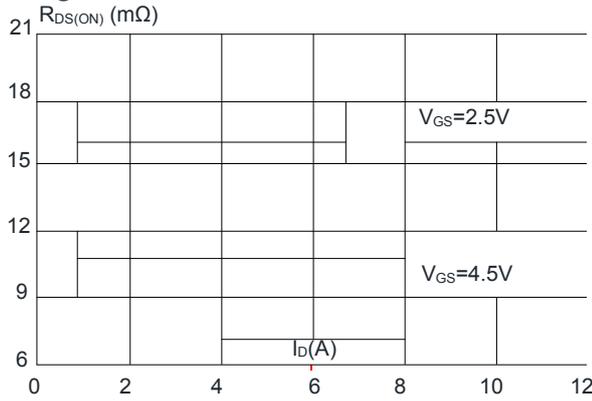
**Figure 1: Output Characteristics**



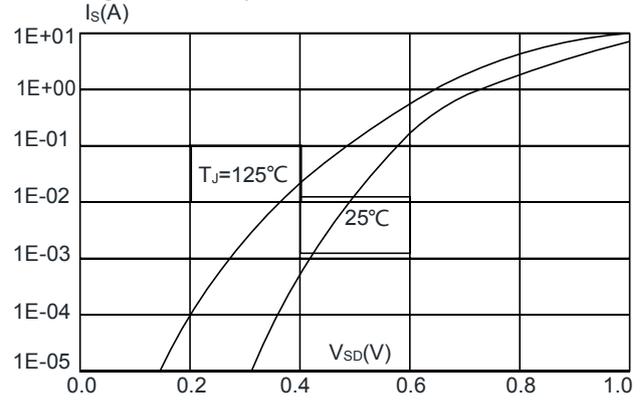
**Figure 2: Typical Transfer Characteristics**



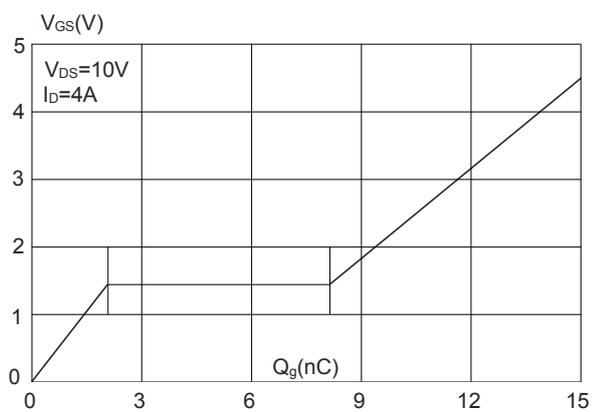
**Figure 3: On-resistance vs. Drain Current**



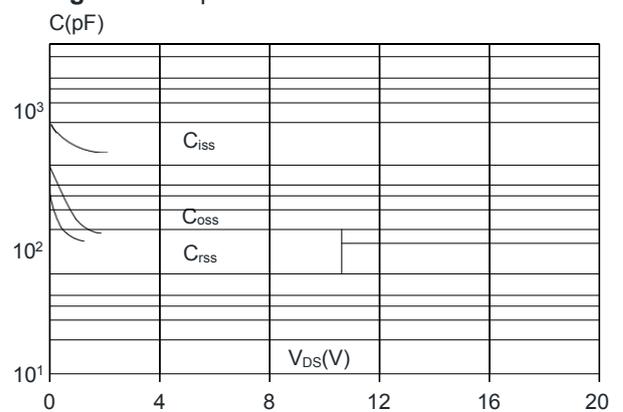
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

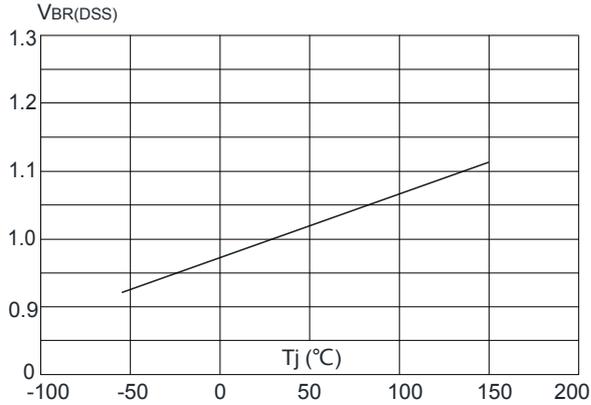


**Figure 6: Capacitance Characteristics**

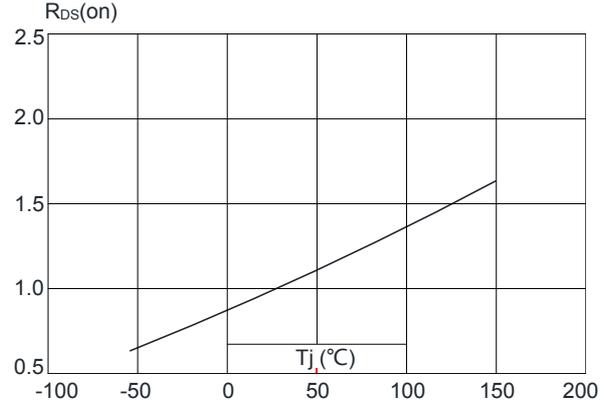


RATING AND CHARACTERISTIC CURVES

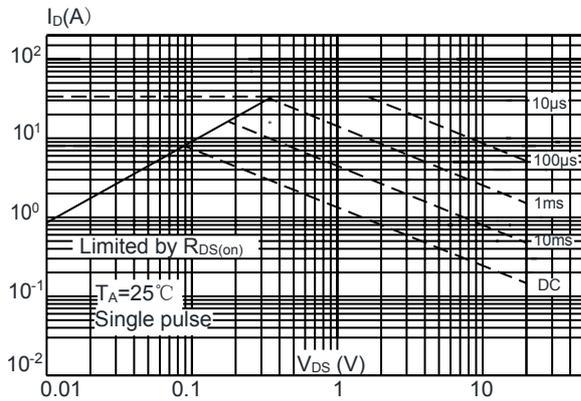
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



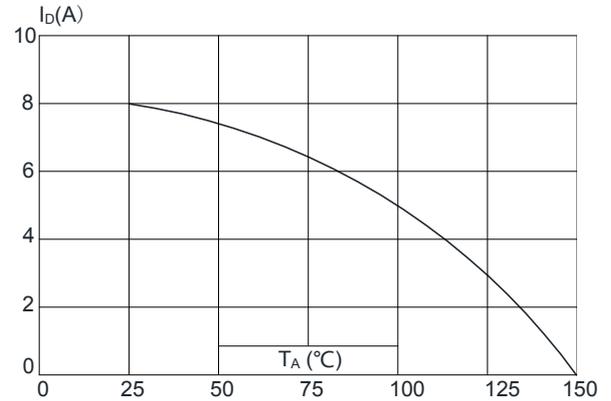
**Figure 8:** Normalized on Resistance vs. Junction Temperature



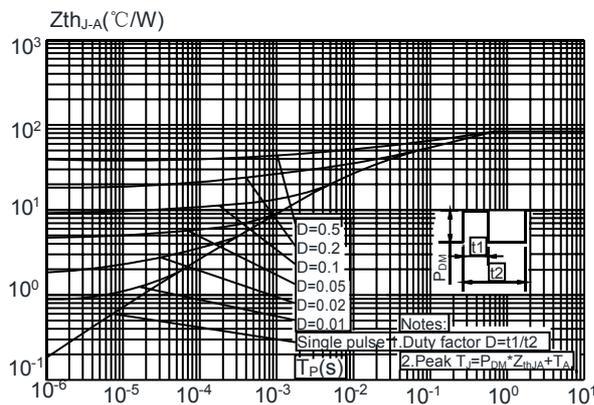
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature

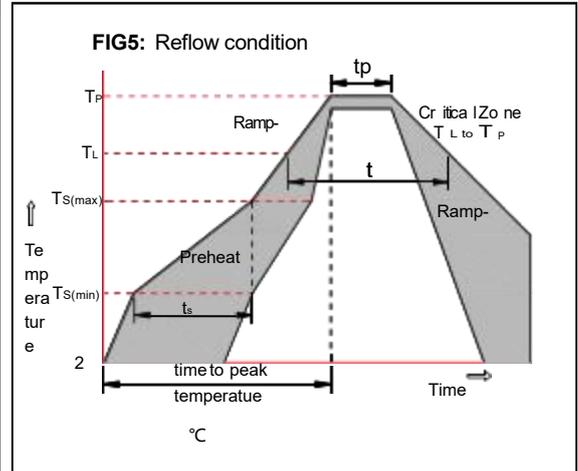


**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



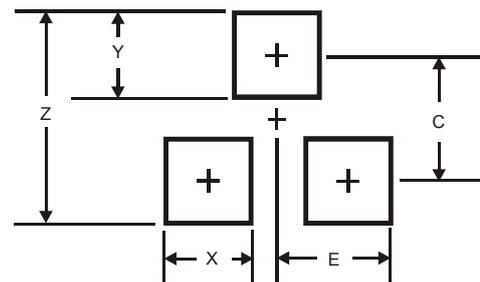
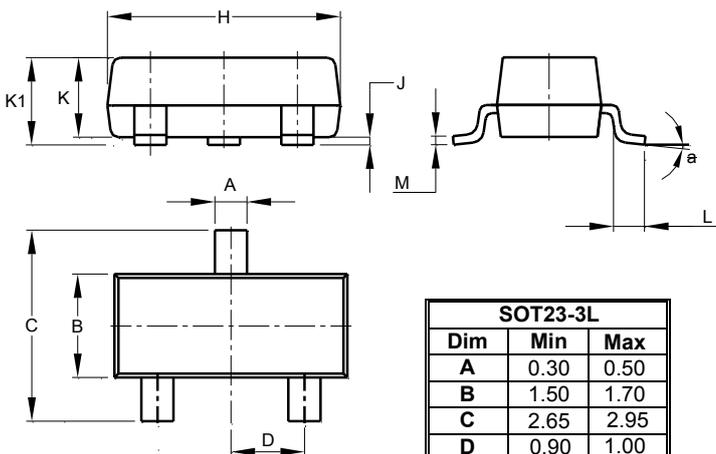
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ( $T_{s(min)}$ )	+150°C
	-Temperature Max( $T_{s(max)}$ )	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp ( $T_L$ ) to peak)		3°C/sec. Max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature( $T_L$ )(Liquid us)	+217°C
	-Temperature( $t_L$ )	60-150 secs.
Peak Temp ( $T_P$ )		+260(+0/-5)°C
Time within 5°C of actual Peak Temp ( $t_p$ )		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp ( $T_P$ )		8 min. Max
Do not exceed		+260°C



Package Dimensions & Suggested Pad Layout

SOT23-3L



Dimensions	SOT23-3L
Z	3.3
X	0.9
Y	1.0
C	2.3
E	1.40

Tape & reel specification

Tape		Symbol	Dimension (mm)		
<p>SECTION : A-A</p> <p>SECTION : B-B</p>		P0	4.00±0.20		
		P1	4.00±0.20		
		P2	2.00±0.20		
		D0	1.55±0.20		
		D1	1.05±0.20		
		E	1.55±0.20		
		F	3.60±0.20		
		W	8.00±0.20		
		A0	3.80±0.20		
		B0	3.50±0.20		
		K0	1.55±0.20		
		T	0.25±0.15		
		7" Reel		D2	178.0±5.0
				D3	55Min.
D4	R24.0±3.0				
G	R82.0±3.0				
I	13.0±2.0				
W1	11.0±3.0				
Quantity: 3000PCS					